
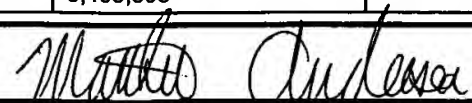


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PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) 		Complete if Known		
		Application Number	10/073,506	
		Filing Date	February 11, 2002	
		Confirmation Number	6190	
		First Named Inventor	Robert J. Falster	
		Group Art Unit	1775	
		Examiner Name		
Sheet	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

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Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
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	2	4,376,657		Nagasawa et al.	03/1983
	3	4,437,922		Bischoff et al.	03/1984
	4	4,505,759		O'Mara	03/1985
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	6	4,851,358		Huber	07/1989
	7	4,868,133		Huber	09/1989
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	15	5,485,803		Habu	01/1996

Examiner Signature		Date Considered	11/20/02
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Examiner Signature	<i>Matthew Anderson</i>	Date Considered	11/20/02
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				Examiner Name	
Sheet	3	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

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Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
45	EP	0 504 837	A2			09/1992	
46	EP	0 503 816	B1			09/1992	
47	EP	0 536 958	A1			04/1993	
48	EP	0 716 168	A1			06/1996	
49	EP	0 747 513	A2		Shin-Estu Handotai Company Ltd.	12/11/1996	
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Examiner Signature <i>Matthew Anderson</i>	Date Considered <i>11/20/02</i>
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				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	
Sheet	4	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

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64	JP	7321120 (Abstract Only)			12/1995	
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68	JP	8-045945			02/1996	

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				First Named Inventor	Robert J. Falster
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MA	69	JP	Hei 8-208374		Nippon Steel Corp. et al	08/13/1996	
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OTHER ART - NON PATENT LITERATURE DOCUMENTS							

Examiner Signature	<i>Matthew Anderson</i>	Date Considered	11/20/02
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				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	
Sheet	6	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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<p>Compl te if Known</p>				Application Number	09/416,998
				Filing Date	October 13, 1998
				Confirmation Number	6867
				First Named Inventor	Robert J. Falster et al.
				Group Art Unit	1765
				Examiner Name	
Sheet	8	of	10	Attorney Docket No.	MEMC 98-1451 (2554.1)

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				Examiner Name	
Sheet	9	of	10	Attorney Docket No.	MEMC 98-1451 (2554.1)

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Examiner Signature	<i>Matthew Anderson</i>	Date Considered	11/20/02
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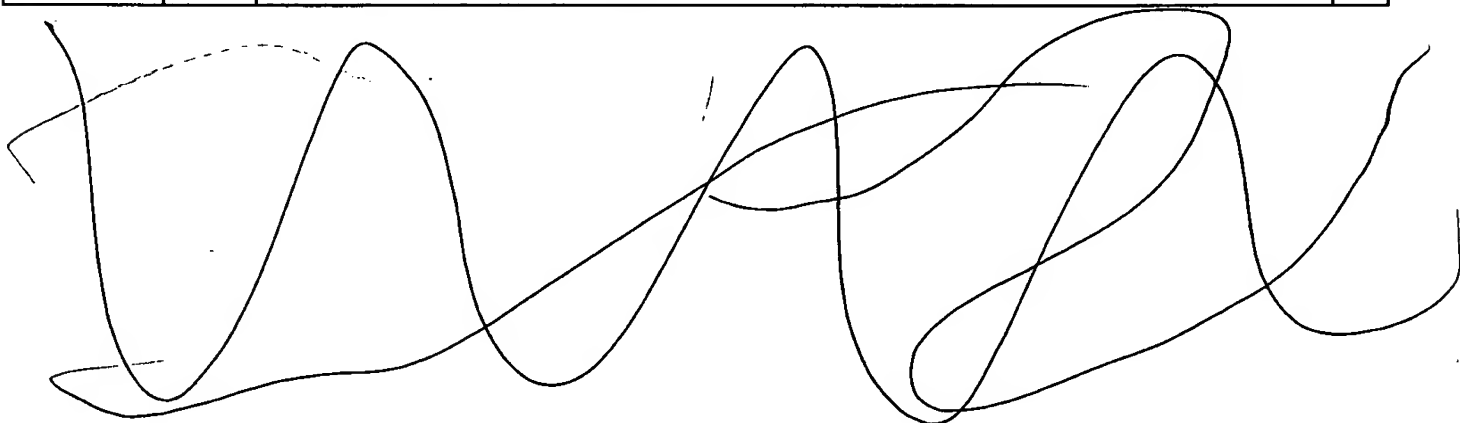
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PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/416,998
				Filing Date	October 13, 1999
				Confirmation Number	6867
				First Named Inventor	Robert J. Falster et al.
				Group Art Unit	1765
				Examiner Name	
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Examiner Signature	<i>Matthew Anderson</i>	Date Considered	1/20/02
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